UMW FDN352AP

-30V P-Channel MOSFET

1.Description

These devices are well suited for low voltage and battery pow-ered applications where low in-line power loss is needed in a very small outline surface mount package.

2.Features

- $V_{DS(V)}$=-30V
- I_D=-1.3A
- $R_{DS(ON)}$(V_{GS}=-10V)≤150mΩ
- $R_{DS(ON)}$(V_{GS}=-4.5V)≤250mΩ

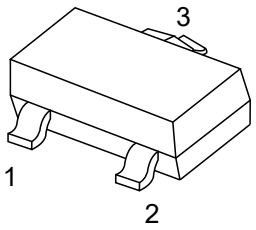
3.Application

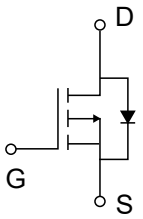
- Notebook computer power management

4.Pinning information

Pin	Symbol	Description
1	G	GATE
2	S	SOURCE
3	D	DRAIN

SOT-23





5.Maximum ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V_{GSS}	±25	V
Drain Current – Continuous (Note 1a)	I_D	-1.3	A
– Pulsed		-10	
Maximum Power Dissipation(Note 1a)	P_D	0.5	W
(Note 1b)		0.46	
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-55 to 150	°C
Thermal Characteristics			
Thermal Resistance, Junction-to-Ambient (Note 1a)	$R_{\theta JA}$	250	°C/W
Thermal Resistance, Junction-to-Case (Note 1)	$R_{\theta JC}$	75	°C/W

6.T_A=25°C unless otherwise specified

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=-250μA, V_{GS}=0V	-30			V
Breakdown Voltage Temperature Coefficient	$\frac{\Delta BV_{DSS}}{\Delta T_J}$	I_D=-250μA Referenced to 25°C		-17		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V, V_{GS}=0V			-1	μA
Gate–Body Leakage	I_{GSS}	V_{GS}=±25V, V_{DS}=0V			±100	nA
On Characteristics (Note 2)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-0.8	-2	-2.5	V
Gate Threshold Voltage Temperature Coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	I_D=-250μA Referenced to 25°C		4		mV/°C
Static Drain–Source On–Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-1.3A		120	150	mΩ
		V_{GS}=-4.5V, I_D=-1.1A		150	250	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V, I_D=-0.9A		2		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=-15V, V_{GS}=0V,f =1MHz		150		pF
Output Capacitance	C_{oss}			40		pF
Reverse Transfer Capacitance	C_{rss}			20		pF
SWITCHING PARAMETERS (Note 2)						
Turn-On DelayTime	$t_{D(on)}$	V_{DD}=-10V, I_D=-1A V_{GS}=-10V, R_{GEN}=6Ω		4	8	ns
Turn-On Rise Time	t_r			15	28	ns
Turn-Off DelayTime	$t_{D(off)}$			10	18	ns
Turn-Off Fall Time	t_f			1	2	ns
Total Gate Charge	Q_g	V_{DS}=-10V, I_D=-0.9A V_{GS}=-4.5V		1.4	1.9	nC
Gate–Source Charge	Q_{gs}			0.5		nC
Gate–Drain Charge	Q_{gd}			0.5		nC

Drain–Source Diode Characteristics and Maximum Ratings						
Maximum Continuous Drain–Source Diode Forward Current	I_S				-0.42	A
Drain–Source Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=-0.42A (Note 2)		-0.8	-1.2	V
Diode Reverse Recovery Time	t_{rr}	I_F=-3.9A		17		ns
Diode Reverse Recovery Charge	Q_{rr}	dI_F/dt=100A/μs		7		nC

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface ofthe drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.

(a) $R_{\theta JA}$ = 250°C/W when mounted on a 0.02 in^2 pad of 2oz. copper.

(b) $R_{\theta JA}$ = 270°C/W when mounted on a 0.001 in^2 pad of 2oz. copper.

2. Pulse Test: Pulse Width < 300μs, Duty Cycle < 2.0%

7.1 Typical Characterisitics

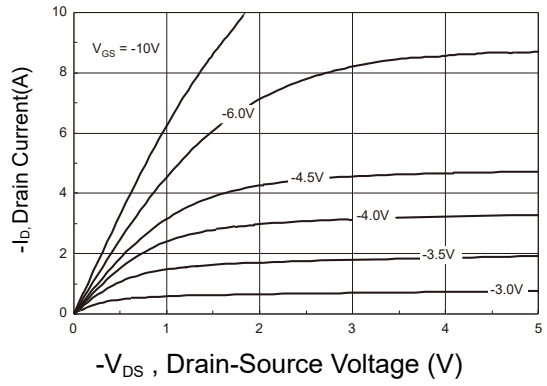


Figure 1: On-Region Characteristics.

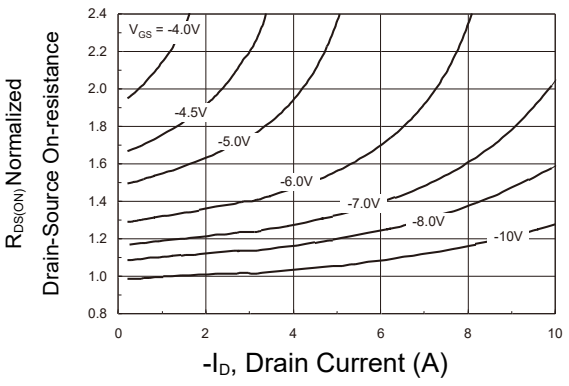


Figure 2: On-Resistance Variation with Drain Current and Gate Voltage.

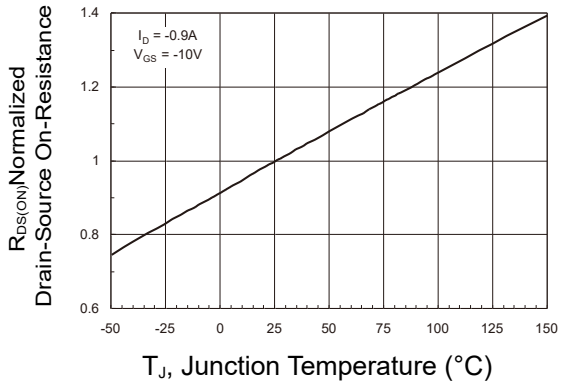


Figure 3: On-Resistance Variation with Temperature.

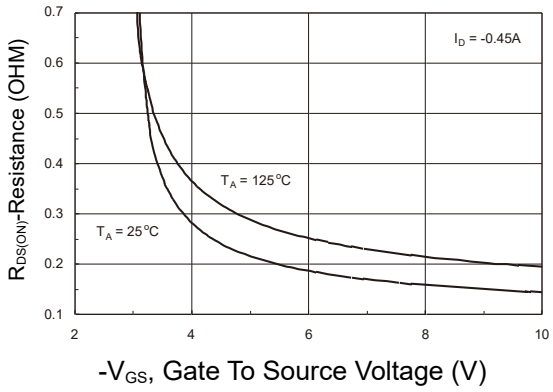


Figure 4: On-Resistance Variation with Gate-to-Source Voltage.

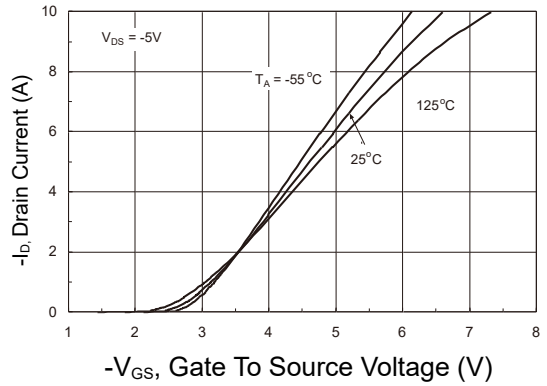


Figure 5: Transfer Characteristics.

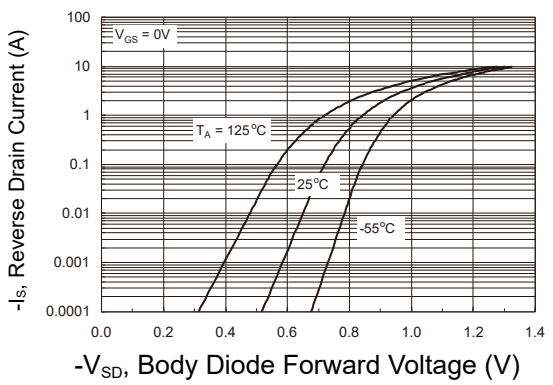


Figure 6: . Body Diode Forward Voltage Variation with Source Current and Temperature.

7.2 Typical Characterisitics

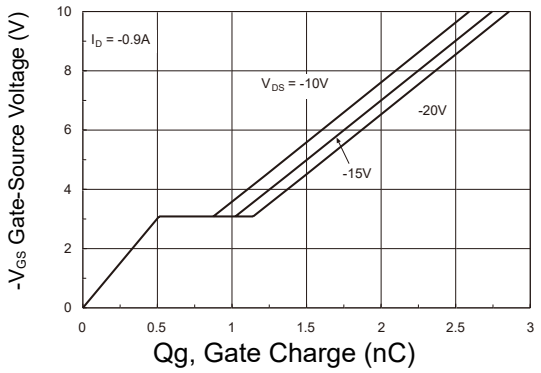


Figure 7: Gate-Charge Characteristics

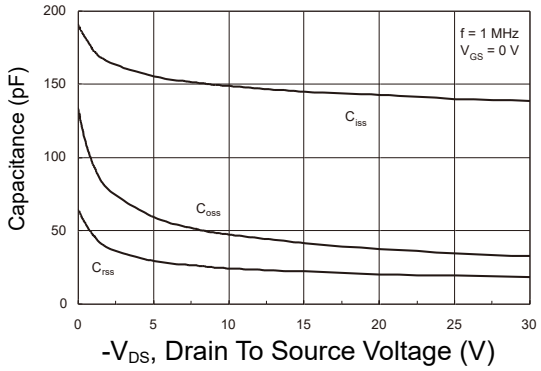


Figure 8: Capacitance Characteristics

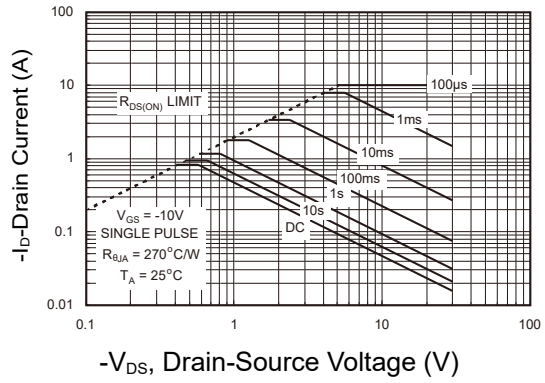


Figure 9: Maximum Safe Operating Area.

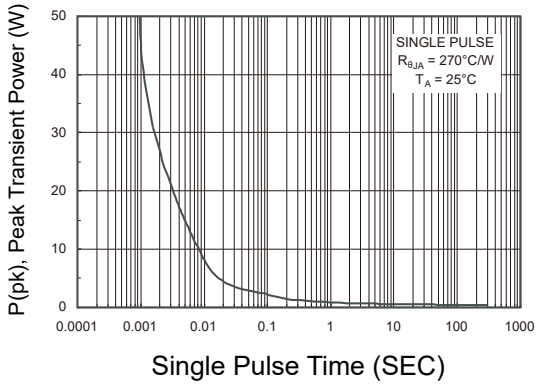


Figure 10: Single Pulse Maximum Power Dissipation.

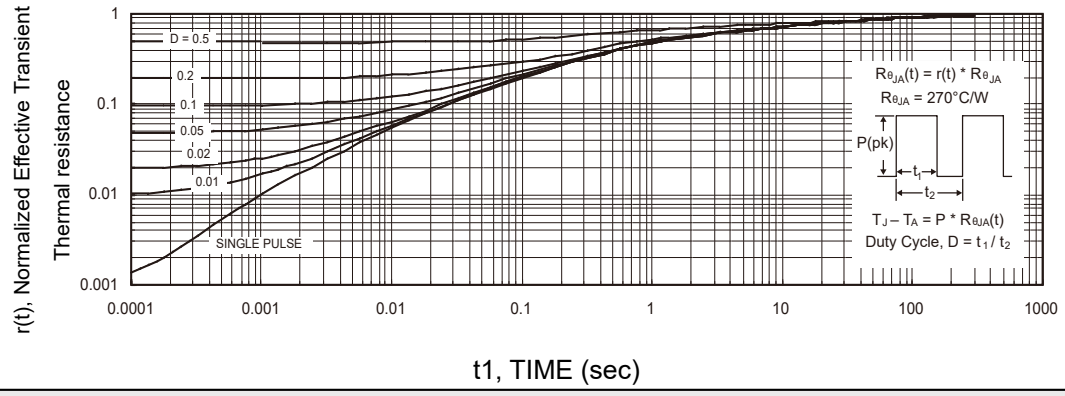
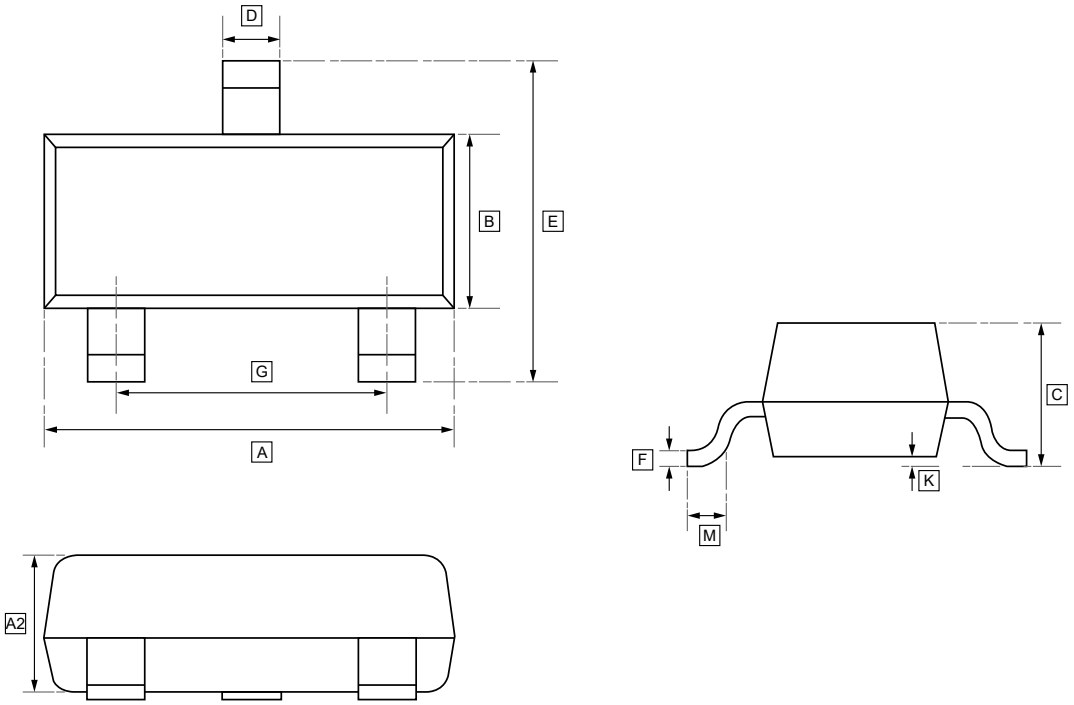


Figure 11. Transient Thermal Response Curve.

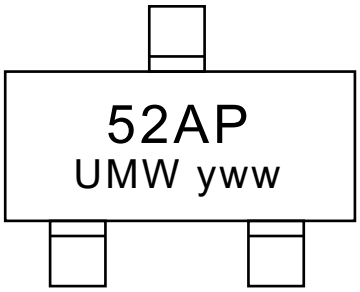
8.SOT-23 Package Outline Dimensions



DIMENSIONS (mm are the original dimensions)

Symbol	A	B	C	D	E	G	K	M	A2	F
Min	2.80	1.20	0.90	0.32	2.25	1.80	0.00	0.30	0.95	0.095
Max	3.04	1.40	1.10	0.55	2.55	2.00	0.10	-	1.05	0.115

9.Ordering Information



yww: Batch Code

Order Code	Package	Base QTY	Delivery Mode
UMW FDN352AP	SOT-23	3000	Tape and reel

10.Disclaimer

UMW reserves the right to make changes to all products, specifications. Customers should obtain the latest version of product documentation and verify the completeness and currency of the information before placing an order.

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